2SB649(A)

Rev.E Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

WR0459I ṂṂ Ł SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

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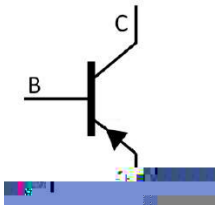
Complementary pair with 2SD669(A).

/ Applications

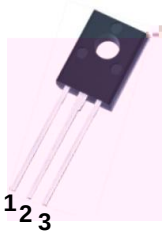
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Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning

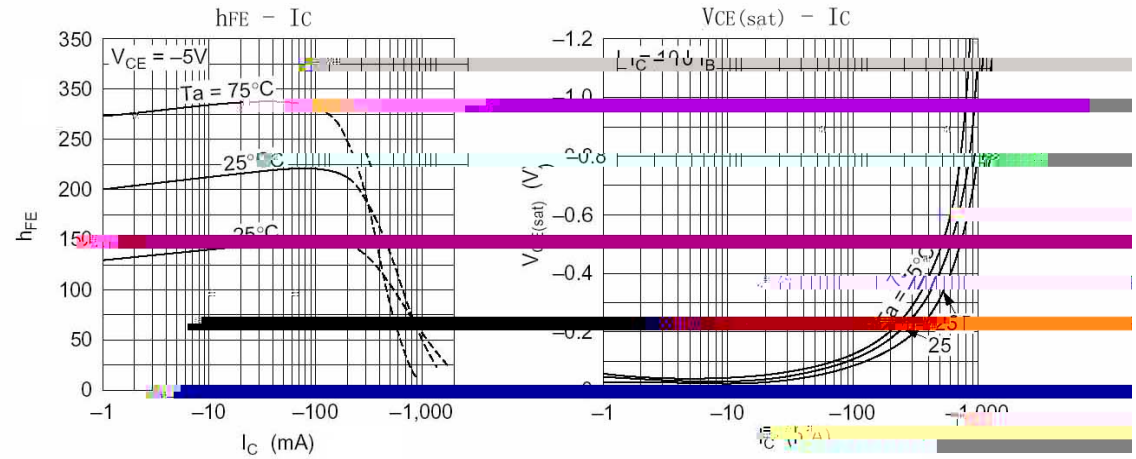


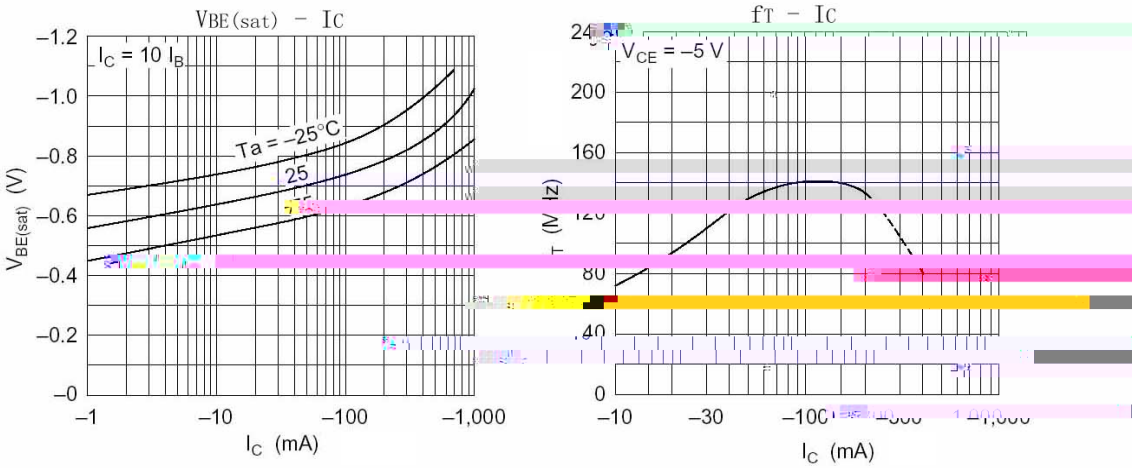
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

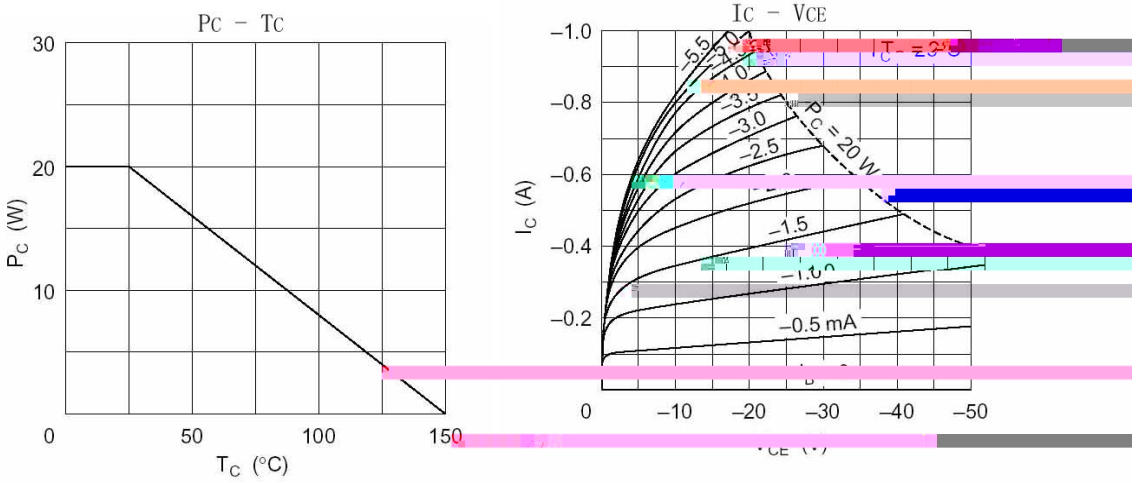
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

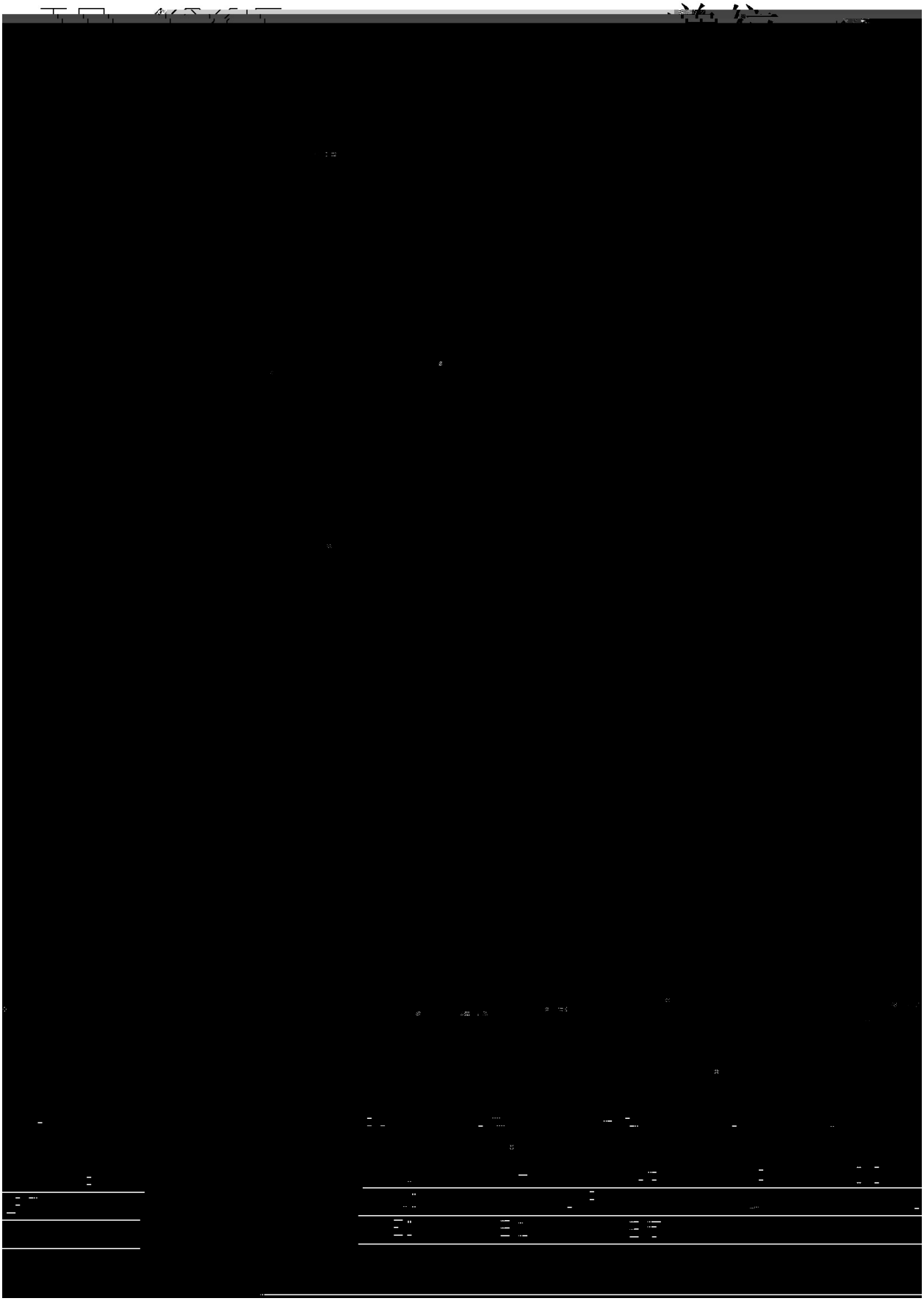
/ Electrical Characteristic Curve



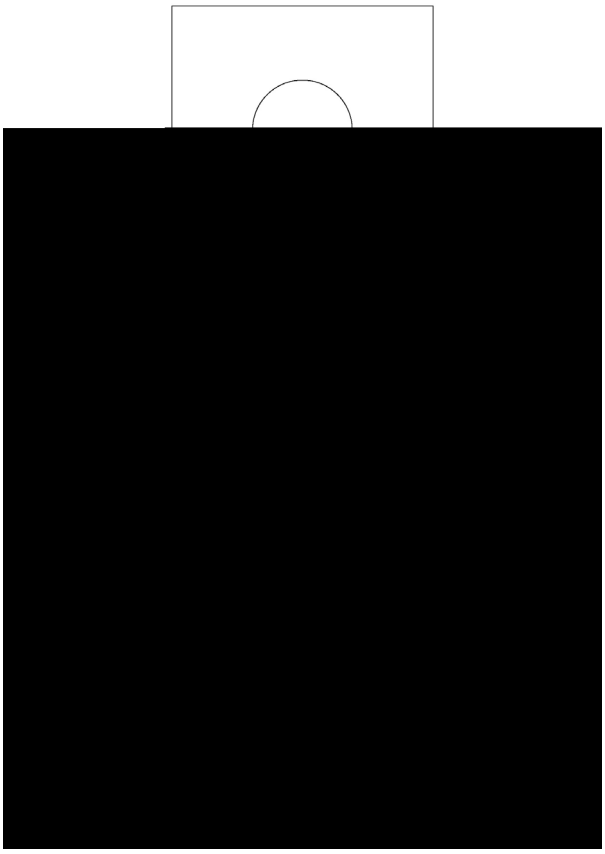




/ Package Dimensions

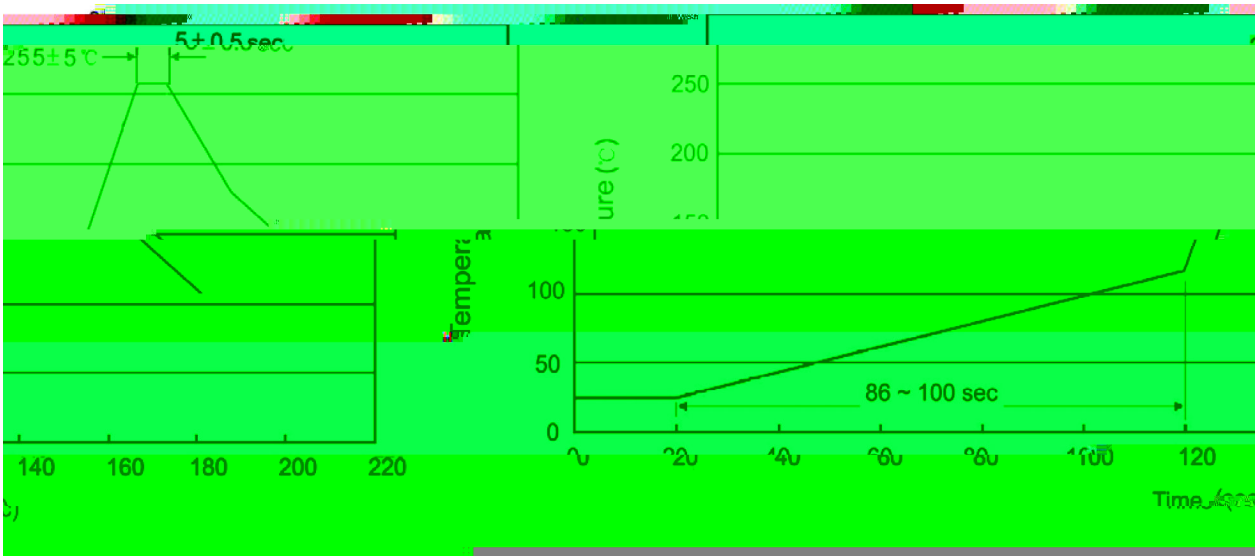


/ Marking Instructions



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EU χ	ѭ ϗ И Ґ
E97< χ	ѭ ϳ N Ґ
E=	ѭ k IH ‘ 6 Ґ
---- χ	ѭ ł ғ ń N Ґ ı ₴ ł ғ ń N Ψ ק
Note:	
BR:	Company Code
B649 :	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ↄ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

5 • **Ủ 2** **õ** ʙ **I** 255 °